

## ABSTRACT

A method for making a semiconductor device is described. That method comprises forming a first dielectric layer on a substrate, then forming a trench within the first dielectric layer. After forming a second dielectric layer on the 5 substrate, a first metal layer is formed within the trench on a first part of the second dielectric layer. A second metal layer is then formed on the first metal layer and on a second part of the second dielectric layer.